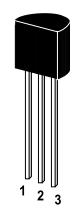
## ST 2SC2001

### NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into three groups, O, Y and G, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

## Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

	Symbol	Value	Unit
Collector Base Voltage	V <sub>CBO</sub>	30	V
Collector Emitter Voltage	V <sub>CEO</sub>	25	V
Emitter Base Voltage	V <sub>EBO</sub>	5	V
Collector Current	Ι <sub>C</sub>	700	mA
Power Dissipation	P <sub>tot</sub>	600	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	Ts	-55 to +150	°C







Dated : 07/12/2002

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### Characteristics at T<sub>amb</sub>=25 °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at V <sub>CE</sub> =1V, I <sub>C</sub> =100mA					
Current Gain Group O	h <sub>FE</sub>	90	-	180	-
Y	h <sub>FE</sub>	135	-	270	-
G	h <sub>FE</sub>	200	-	400	-
at $V_{CE}$ =1V, I <sub>C</sub> =700mA	h <sub>FE</sub>	50	-	-	-
Collector Base Breakdown Voltage					
at I <sub>C</sub> =10μA	V <sub>(BR)CBO</sub>	30	-	-	V
Base Emitter Voltage					
at I <sub>C</sub> =10mA, V <sub>CE</sub> =6V	V <sub>BE</sub>	0.6	-	0.7	V
Emitter Cutoff Current					
at V <sub>EB</sub> =5V	I <sub>EBO</sub>	-	-	0.1	μA
Collector Cutoff Current					
at V <sub>CB</sub> =30V	I <sub>CBO</sub>	-	-	0.1	μA
Collector Saturation Voltage					
at I <sub>C</sub> =700mA, I <sub>B</sub> =70mA	V <sub>CE(sat)</sub>	-	0.2	0.6	V
Base Saturation Voltage					
at I <sub>C</sub> =700mA, I <sub>B</sub> =70mA	V <sub>BE(sat)</sub>	-	0.95	1.2	V
Gain Bandwidth Product					
at $V_{CE}$ =6V, $I_C$ =10mA	f⊤	50	170	-	MHz
Output Capacitance					
at V <sub>CB</sub> =6V, f=1MHz	C <sub>OB</sub>	-	13	25	pF







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